

Abstract of the Disclosure

A phase edge phase shift mask is capable of providing photoresist patterns having a variety of sizes and pitches. The phase edge phase shift mask is formed from a quartz substrate. The substrate is etched to provide a trench therein of a depth that will induce a 180° phase shift in exposure light. An auxiliary pattern is formed on a portion of the top of the quartz substrate and/or on a portion of the substrate at the bottom of the trench as spaced from the sidewall surface of the substrate that defines the sides of the trench. The auxiliary pattern is formed of either an optical interference material or an opaque material.